FM30N25EQ/T

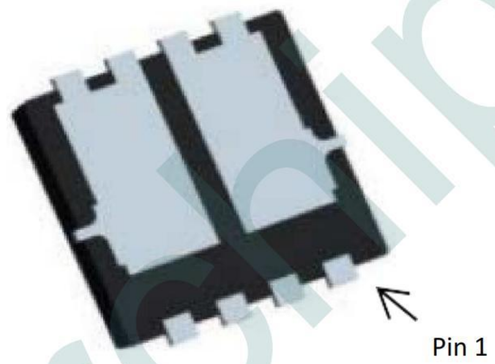
N-Channel Enhancement Mode MOSFET

- 30V,25A
- $R_{DS(ON)}$=9.3mΩ (Typ.) @ V_{GS} =10V
- $R_{DS(ON)}$=13mΩ (Typ.) @ V_{GS} =4.5V
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current

Application

- LCD TV
- Notebook
- Elevator
- Inductive heating Power tools
- Power tools

Package



PDFN3*3

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	25	A
		T_C = 100℃	15	A
I_{DM}	Pulsed Drain Current note1		80	A
E_{AS}	Single Pulsed Avalanche Energy note2		58	mJ
P_D	Power Dissipation	T_C = 25℃	27	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.21	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-50 to +150	℃

www.superchip.cn